

Quarterly Reliability Monitoring Results

Quarters: Q1/2023 to Q4/2024

Based on structural similarity

Supplier		User Part Number				
Nexperia B.V.		PMEG2002AESF				
Name of Laboratory		Part Description				
Assembly reliability labs		Nexperia DHAM Schottky BD				
Test	Test Conditions	Duration	# Lots	# Quantity	# Rejects	
# 1	TEST Pre- and Post-Stress Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below
# 5	HTRB High Temperature Reverse Bias	MIL-STD-750-1 M1038 Method A Tj = Tjmax, Vr = 100% of max. datasheet reverse voltage ^[1]	1000 hours	79	3160	0
# 7	TC Temperature Cycling	JESD22-A104 -40 °C to 125°C	1000 cycles	79	3160	0
# 8 or	UHAST Unbiased HAST	JESD22-A118 Tamb = 130 °C, RH = 85 %	96 hours	n.a.	n.a.	n.a.
# 8a	AC Autoclave	JESD22-A102 Tamb = 121 °C, RH = 100 % Pressure = 205 kPa (29.7 psia)				
# 9	H3TRB High Humidity High Temperature Reverse Bias	JESD22-A101 Tamb = 85 °C, RH = 85%, VR = 80 % of rated reverse voltage ^{[1], [2]}	1000 hours	n.a.	n.a.	n.a.
# 10	IOL Intermittent Operating Life	MIL-STD-750 Method 1037 ton = toff, devices powered to insure ΔTj = 100 °C	333 hours	79	3160	0
# 20	RSH Resistance to Solder Heat	JESD22-A111 260 °C ± 5 °C	10 s	n.a.	n.a.	n.a.
# 21	SD Solderability	J-STD-002		19	570	0

[1] The physical limitations of Schottky diodes have to be considered (thermal runaway).

[2] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test # 5)

Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia DHAM	Schottky	3160	0	1,34	7,44E+08